

Supplementary material

SiO_x Anode Strengthened by Self-Catalytic Growth of Carbon Nanotubes

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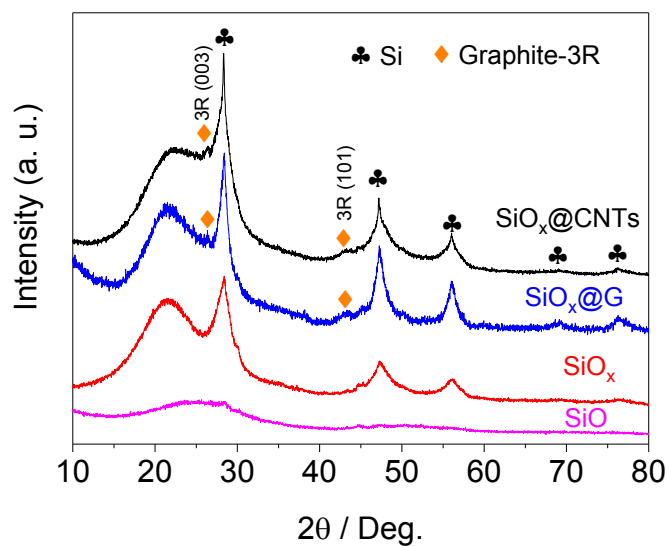


Figure S1. XRD patterns of SiO, SiO_x, SiO_x@G, and SiO_x@CNTs.

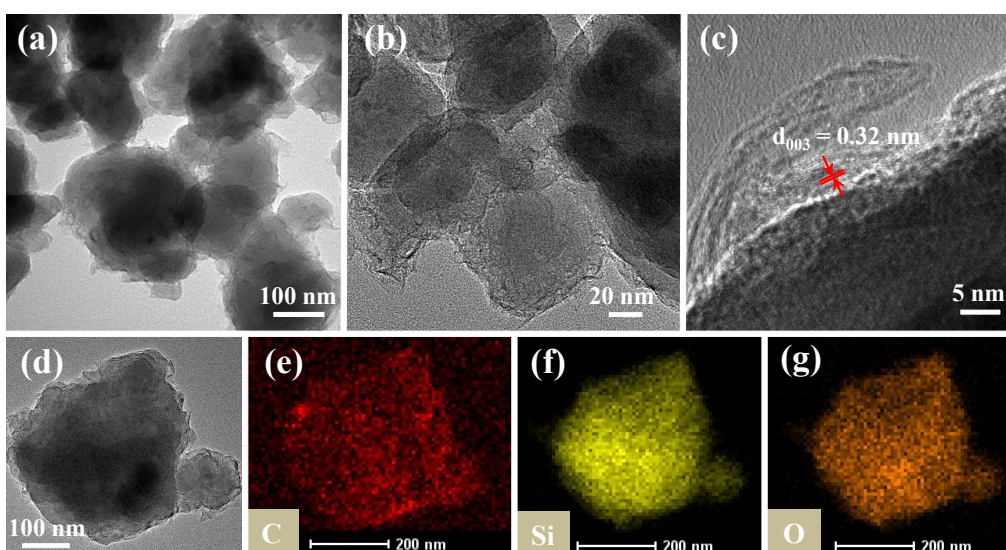


Figure S2. (a,b) TEM images and (c) high-resolution TEM image of $\text{SiO}_x@\text{G}$. (d-g) TEM image and EDS elemental mapping images of C, Si, and O of $\text{SiO}_x@\text{G}$.

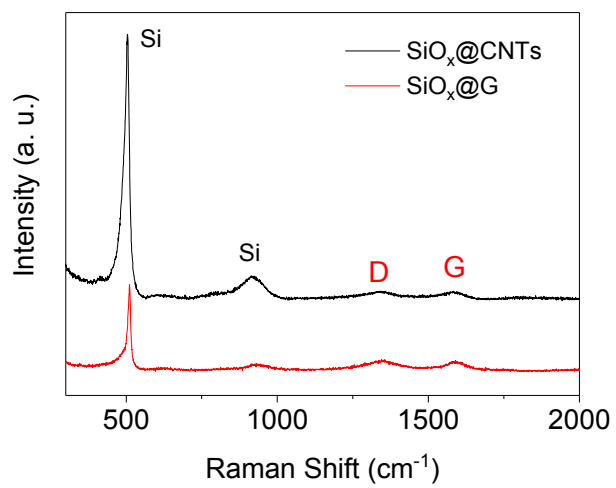


Figure S3. Raman spectra of SiO_x@CNTs and SiO_x@G.

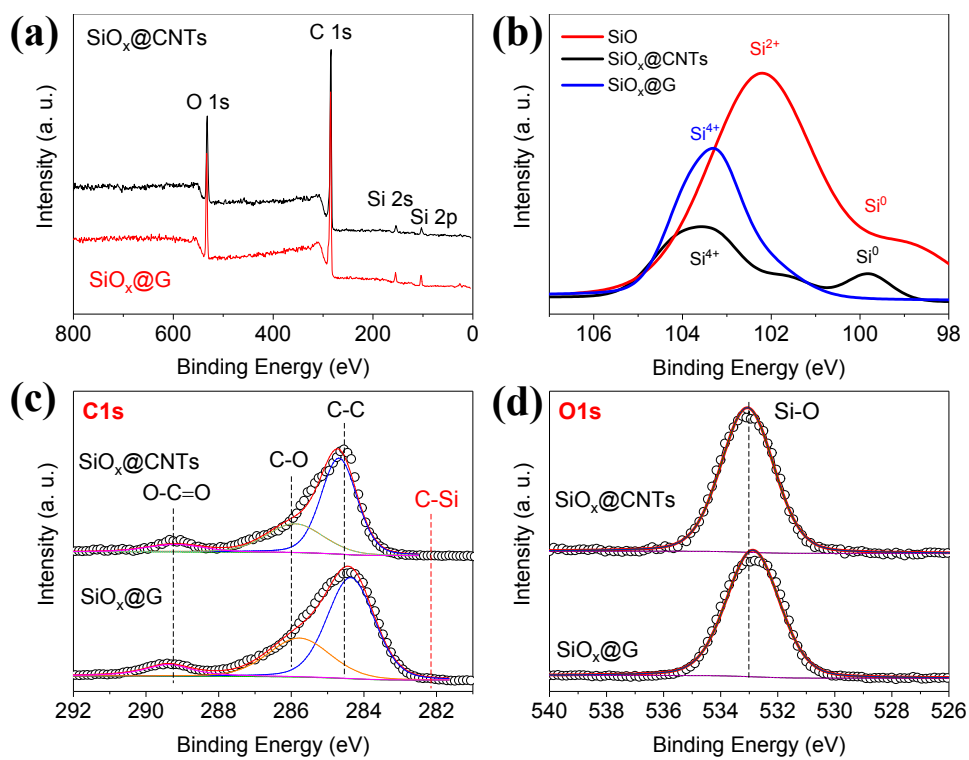


Figure S4. (a) XPS survey spectra of SiO_x@CNTs and SiO_x@G. High resolution XPS spectra of (b) Si2p/Si2s, (c) C1s, and (d) O1s of SiO_x@CNTs and SiO_x@G.

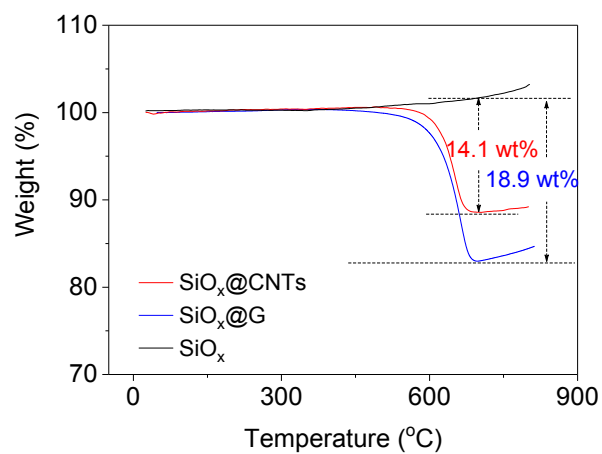


Figure S5. TGA profiles of SiO_x@CNTs, SiO_x@G and SiO_x.

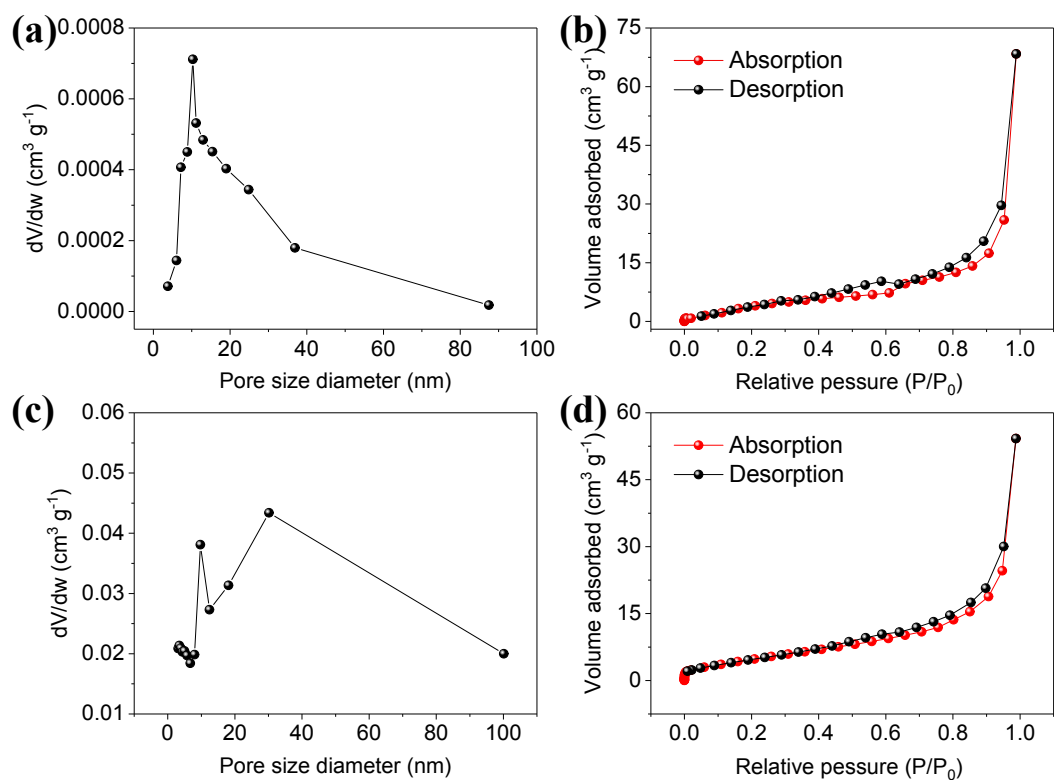


Figure S6. N₂ adsorption/desorption isotherms and pore size distribution curves of (a,b) SiO_x@CNTs and (c,d) SiO_x@G.

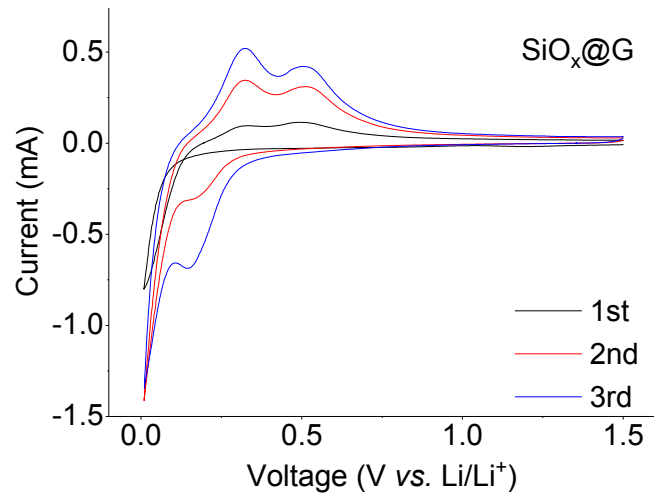


Figure S7. CV curves of $\text{SiO}_x@\text{G}$ at a scan rate of 0.1 mV s^{-1} .

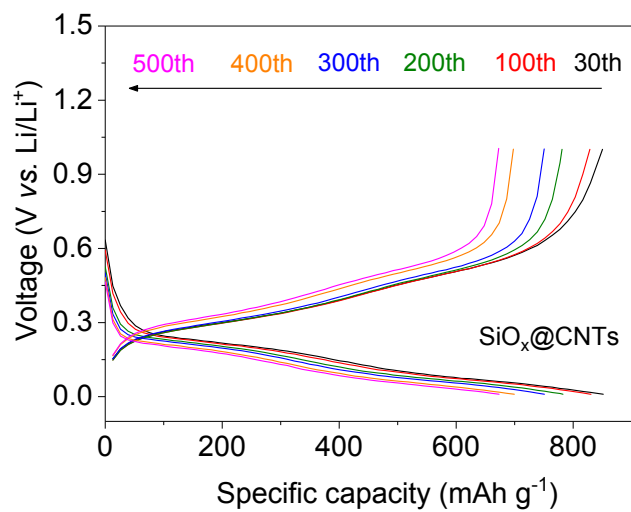


Figure S8. Typical voltage vs. capacity profiles of SiO_x@CNTs in the cycle test.

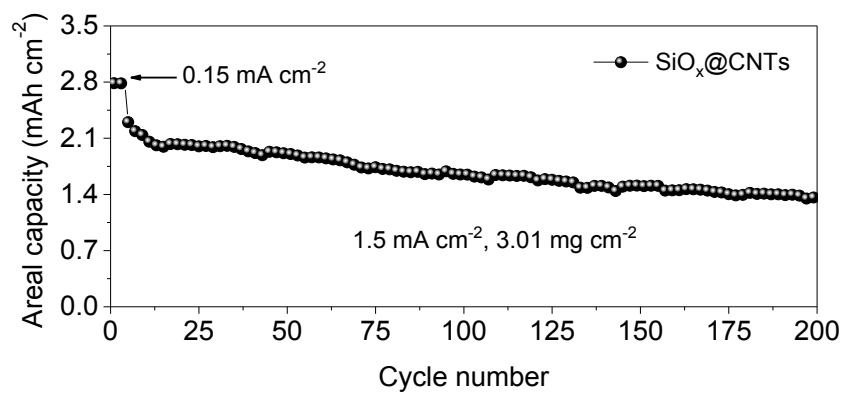


Figure S9. Cycle performance of SiO_x@CNTs at a current density of 1.5 mA cm⁻².

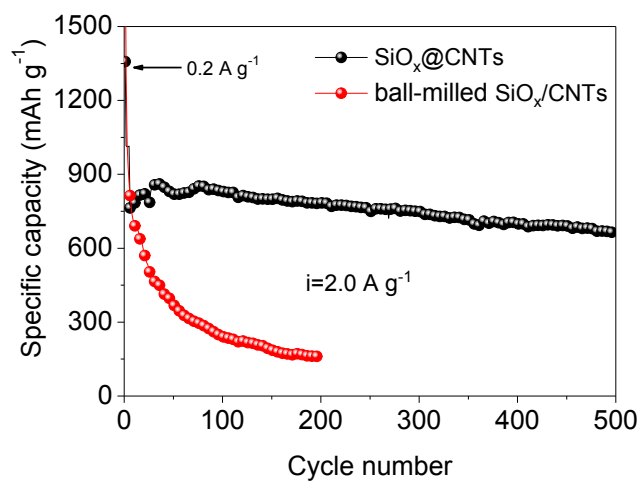


Figure S10. Comparative cycle performance of the SiO_x@CNTs and ball-milled SiO_x/CNTs at a current density of 2 A g⁻¹.

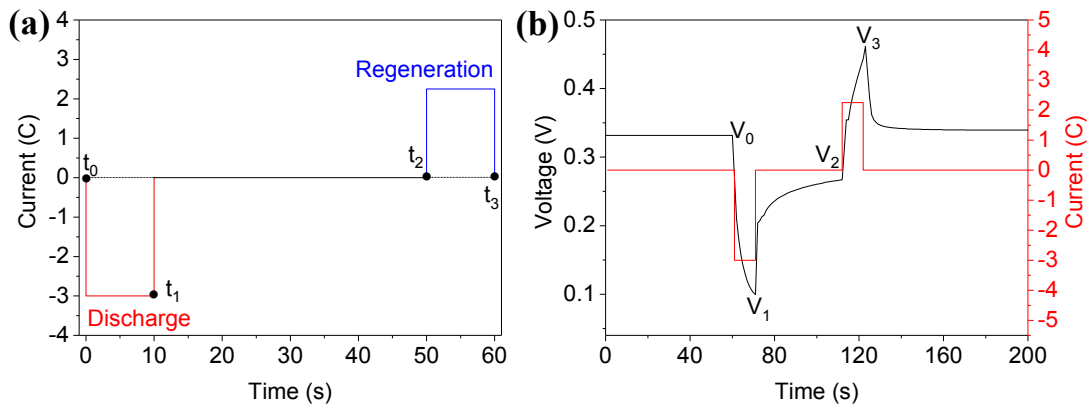


Figure S11. Method of the HPPC test. (a) The battery was pulse discharged for 10 s at a rate of 3 C, which was subsequently relaxed at the open-circuit voltage (OCV) for 40 s, and then charged for 10 s with a regenerative pulse at 75% current (2.25 C rate) of the discharge pulse. The discharge procedure was repeated from 10 to 90% depth of discharge (DOD), which was followed by a 1 h rest period before applying the next sequence. (b) One sequence under 20% DOD.

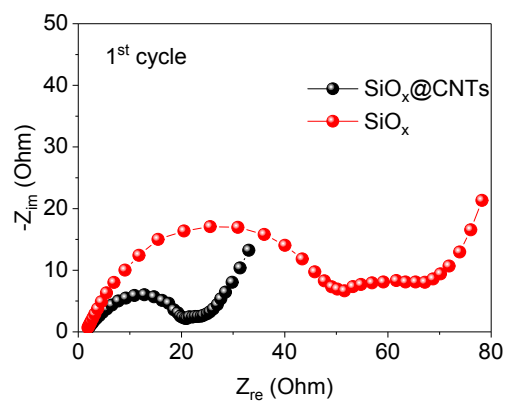


Figure S12. Nyquist plots of SiO_x@CNTs and SiO_x electrodes after the 1st cycle.

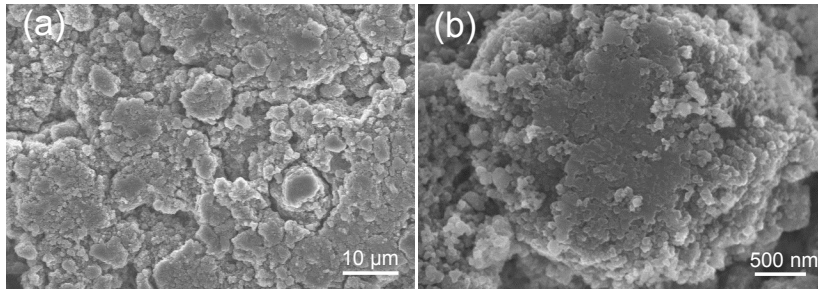


Figure S13. Ex-situ SEM images of SiO_x@G anode after 100 cycles.

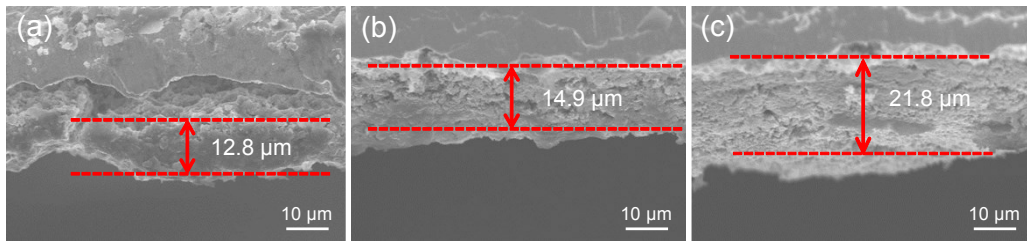


Figure S14. Cross-sectional SEM images of (a) electrode before cycling, and (b) SiO_x and (c) $\text{SiO}_x@\text{CNTs}$ electrodes after 100 cycles.

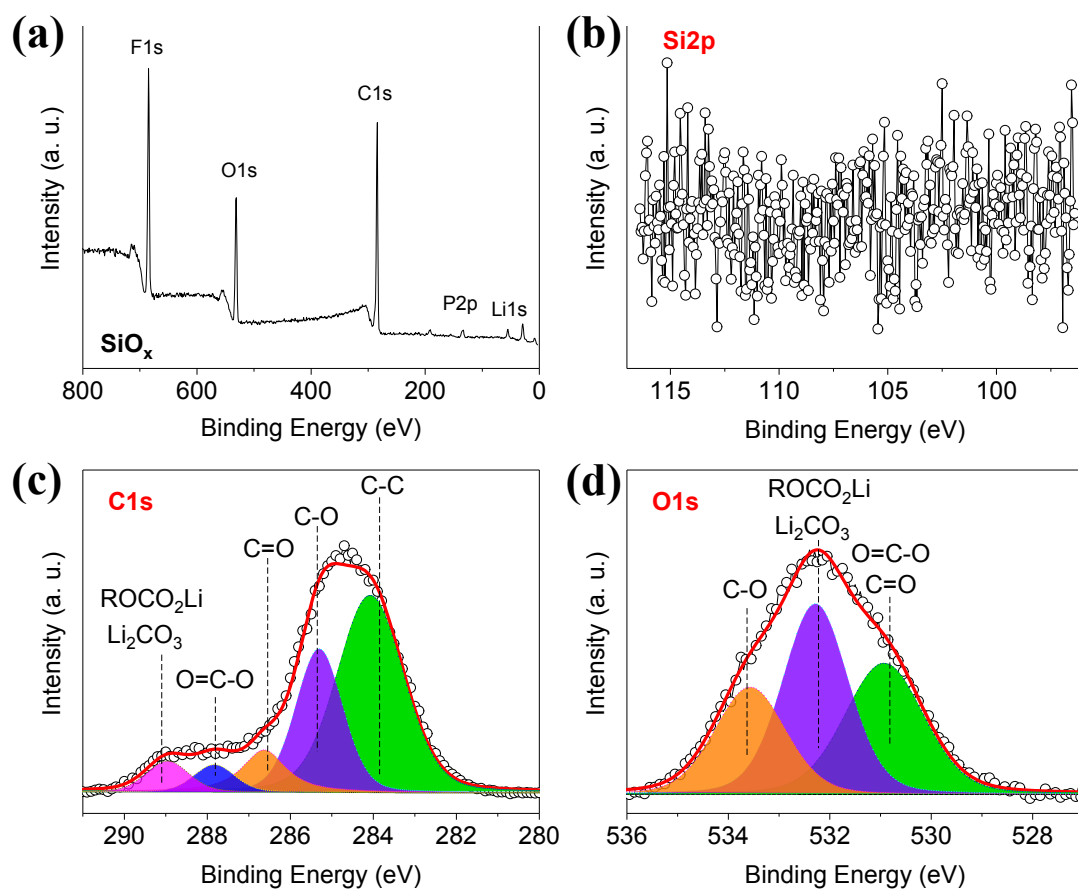


Figure S15. Surface layer characterization of the SiO_x electrode after 100 cycles. (a) Full XPS spectrum and XPS expanded spectra of (b) Si2p, (c) C1s, and (d) O1s.

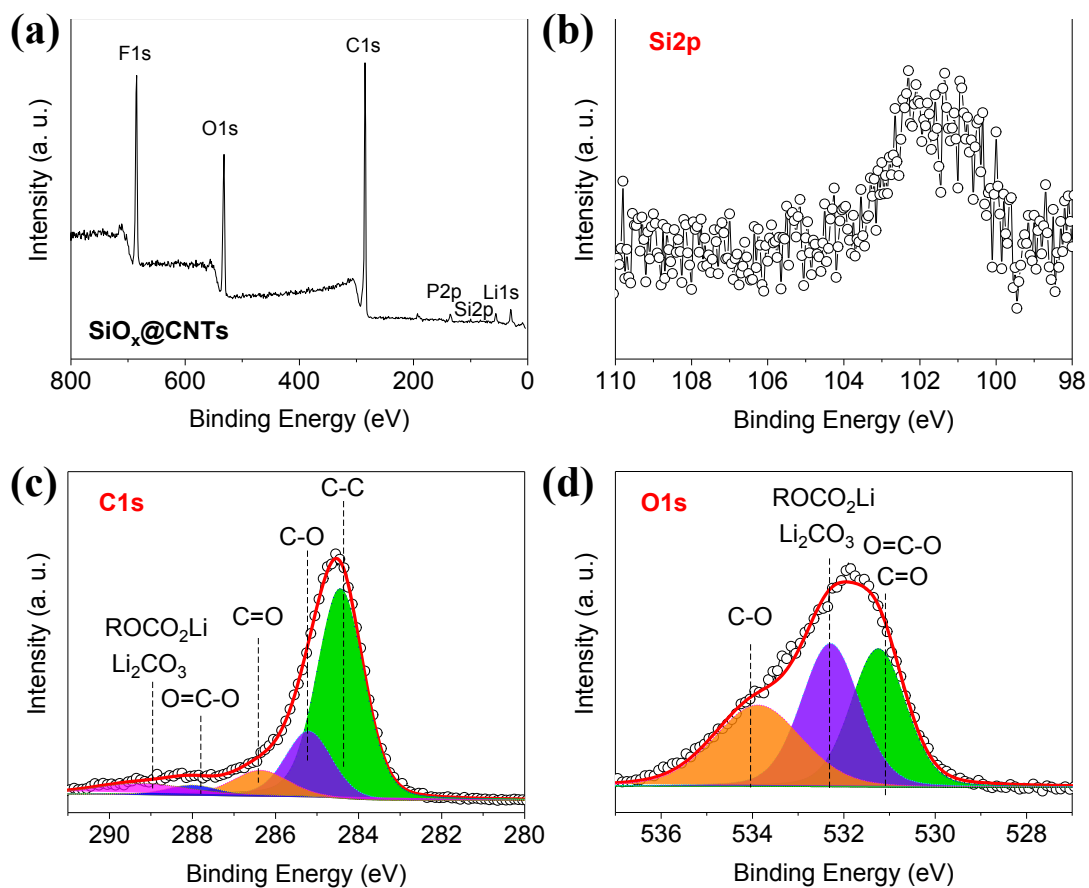


Figure S16. Surface layer characterization of the $\text{SiO}_x\text{@CNTs}$ electrode after 100 cycles. (a) Full XPS spectrum and XPS expanded spectra of (b) Si2p, (c) C1s, and (d) O1s.

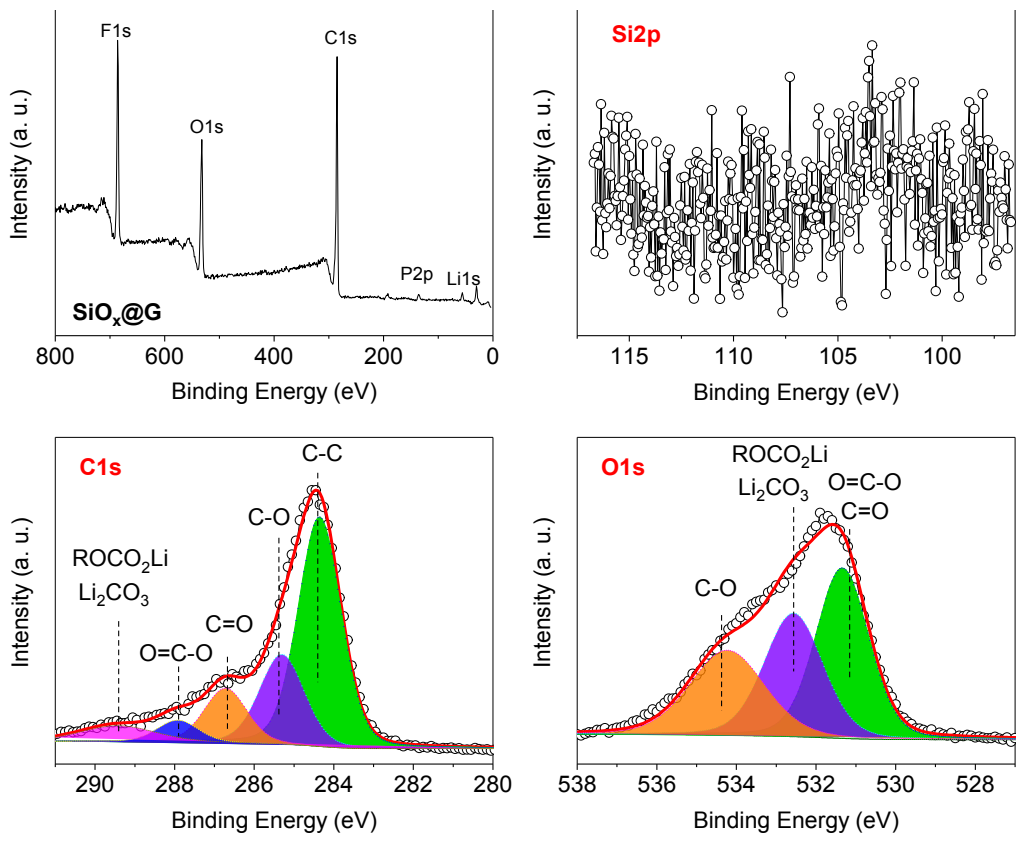


Figure S17. Surface layer characterization of the SiO_x@G electrode after 100 cycles. (a) Full XPS spectrum and XPS expanded spectra of (b) Si2p, (c) C1s, and (d) O1s.

Table S1. Comparative electrochemical performance of the as-prepared SiO_x@CNTs and those of the SiO_x-based composites reported previously.

Materials	Current density (A g ⁻¹)	Cycle numbers	Capacity (mAh g ⁻¹)	Retention	Ref.
SiO _x /G/C	0.12	500	487	74.6%	[1]
SiO _x /C spheres	1	400	493	80.9%	[2]
VG@SiO _x /NC	2	500	642	84.2%	[3]
SiO/Sn	0.2	100	850	60.0%	[4]
YS-SiO _x /C@C	0.5	1000	557	76.4%	[5]
SiO _x -C	0.1	100	674	83.5	[6]
p-SiO _x @TiO ₂ @C	0.7	500	588	61.1%	[7]
SiO_x@CNTs composites	2	500	673	89.1	This work

The energy density of the full cell is calculated by the following equation:

$$\text{Energy Density} = \frac{C_{\text{cathode}} \times C_{\text{anode}}}{C_{\text{cathode}} + C_{\text{anode}}} \times V_{\text{nominal}}$$

where C_{cathode} , C_{anode} , and V_{nominal} are 173 mAh g⁻¹, 1012 mAh g⁻¹, and 3.4 V respectively.

For example, the energy density of the full cell at 0.3 C is:

$$\text{Energy Density} = \frac{173 \text{ mAh g}^{-1} \times 1012 \text{ mAh g}^{-1}}{173 \text{ mAh g}^{-1} + 1012 \text{ mAh g}^{-1}} \times 3.4 \text{ V} = 502.3 \text{ Wh kg}^{-1}$$

References

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